

**Silicon Carbide (SiC)**  
**MOSFET – 80 mohm,**  
**1200 V, M1, TO-247-3L**  
**NVHL080N120SC1A**

- Typ.  $R_{DS(on)} = 80 \text{ m}\Omega$
- Ultra Low Gate Charge (typ.  $Q_{G(tot)} = 56 \text{ nC}$ )
- Low Effective Output Capacitance (typ.  $C_{oss} = 80 \text{ pF}$ )
- 100% UIL Tested
- AEC-Q101 Qualified and PPAP Capable
- This Device is Halide Free and RoHS Compliant with exemption 7a, Pb-Free 2LI (on second level interconnection)
  
- Automotive On Board Charger
- Automotive DC-DC converter for EV/HEV



--				
--			-	
--			-	
$\theta$				
$\theta$				
$\theta$				
$\theta$				
			-	

--  
i











**onsemi**, **onsemi**, and other names, marks, and brands are registered and/or common law trademarks of Semiconductor Components Industries, LLC dba "**onsemi**" or its affiliates and/or subsidiaries in the United States and/or other countries. **onsemi** owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of **onsemi**'s product/patent coverage may be accessed at [www.onsemi.com/site/pdf/Patent-Marking.pdf](http://www.onsemi.com/site/pdf/Patent-Marking.pdf). **onsemi** reserves the right to make changes at any time to any products or information herein, without notice. The information herein is provided "as-is" and **onsemi** makes no warranty, representation or guarantee regarding the accuracy of the information, product features, availability, functionality, or suitability of its products for any particular purpose, nor does **onsemi** assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. Buyer is responsible for its products and applications using **onsemi**

---

---